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February 2009

FPF2174 IntelliMAX[™] Advanced Load Management Products

Features

- 1.8 to 5.5V Input Voltage Range
- Controlled Turn-On
- 200mA Current Limit Option
- Undervoltage Lockout
- Thermal Shutdown
- <1µA Shutdown Current</p>
- Fast Current limit Response Time
 - 3µs to Moderate Over Currents
 - 20ns to Hard Shorts
- Integrated very low V_F Schottky Diode for **Reverse Current Blocking**
- Integrated Zener Diode for Output Clamp
- RoHS Compliant

Applications

- PDAs
- Cell Phones
- GPS Devices
- MP3 Players
- Digital Cameras
- Peripheral Ports
- Hot Swap Supplies

General Description

The FPF2174 is a load switch which combines the functionality of the IntelliMAX $^{\rm TM}$ series load switch with a very low forward voltage drop Schottky barrier rectifier and a zener clamp at the output. The integrated solution provides full protection to systems and loads which may encounter large current conditions in a very compact MLP 3x3 package. This device contain a 0.125Ω current-limited P-channel MOSFET which can operate over an input voltage range of 1.8-5.5V. The Schottky diode acts as a barrier so that no reverse current can flow when the MOSFET is off and the output voltage is higher than the input voltage. Switch control is by a logic input (ON) capable of interfacing directly with low voltage control signals. Each part contains thermal shutdown protection which shuts off the switch to prevent damage to the part when a continuous over-current condition causes excessive heating.

When the switch current reaches the current limit, the part operates in a constant-current mode to prohibit excessive currents from causing damage. If the constant current condition still persists after 10ms, these parts will shut off the switch and pull the fault signal pin (FLAGB) low. The switch will remain off until the ON pin is cycled. The minimum current limit is 200mA.

These parts are available in a space-saving 6L MLP 3x3 package.

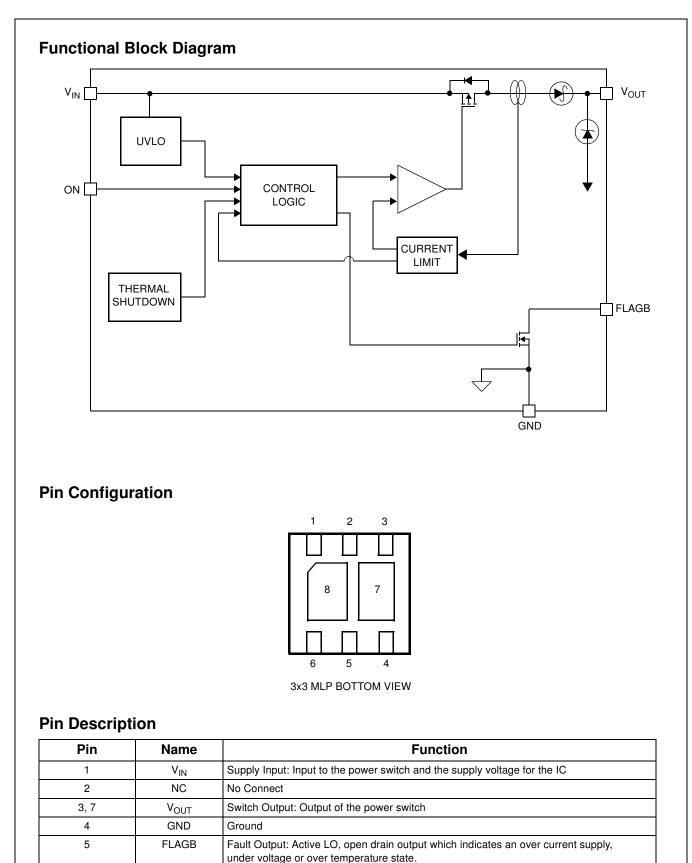
Typical Application Circuit TO LOAD VIN VOUT FPF2174 OFF ON ON FLAGB GND

Ordering Information

Part	Current Limit Min [mA]	Current Limit Blanking Time Typ [ms]	Auto-Restart Time [ms]	ON Pin Activity	Top Mark
FPF2174	200	10	NA	Active HI	2174

1





6

8

IC substrate. Can be connected to GND. Do not connect to other pins.

ON Control Input

ON

PAD1

Absolute Maximum Ratings

Parameter	Min	Max	Unit	
V _{IN} , ON, FLAGB to GND		-0.3	6	V
V _{OUT} to GND	-0.3	20	V	
Power Dissipation @ $T_A = 25 \degree C$ (note 1)		-	1.4	W
Operating Temperature Range	-40	85	°C	
Storage Temperature	-65	150	°C	
Thermal Resistance, Junction to Ambient	-	70	°C/W	
Electrostatic Discharge Protection	HBM	4000	-	V
	MM	400	-	V

Recommended Operating Range

Parameter	Min	Max	Unit
V _{IN}	1.8	5.5	V
Ambient Operating Temperature, T _A	-40	85	°C

Electrical Characteristics

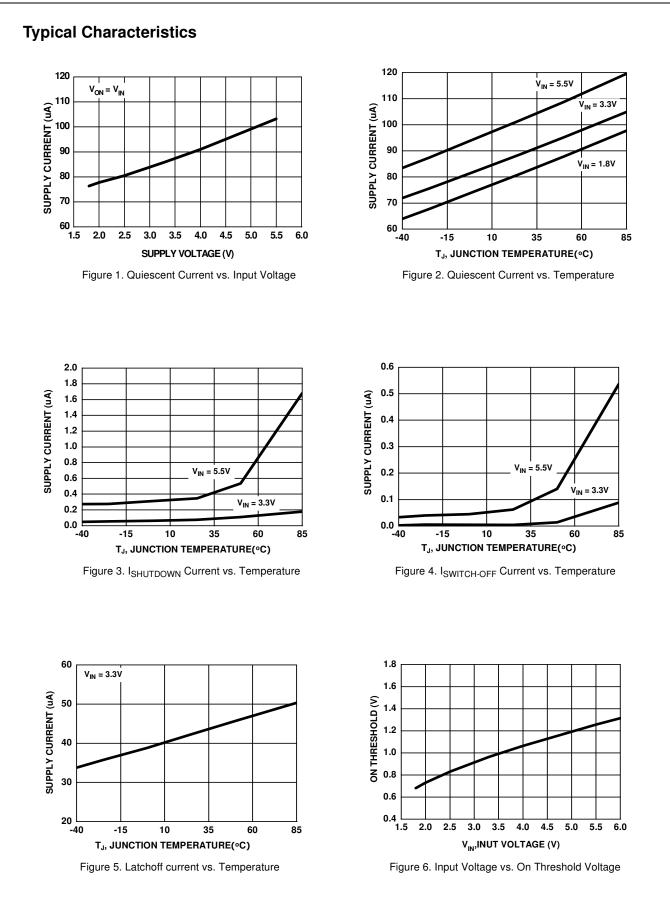
 V_{IN} = 1.8 to 5.5V, T_A = -40 to +85 °C unless otherwise noted. Typical values are at V_{IN} = 3.3V and T_A = 25 °C.

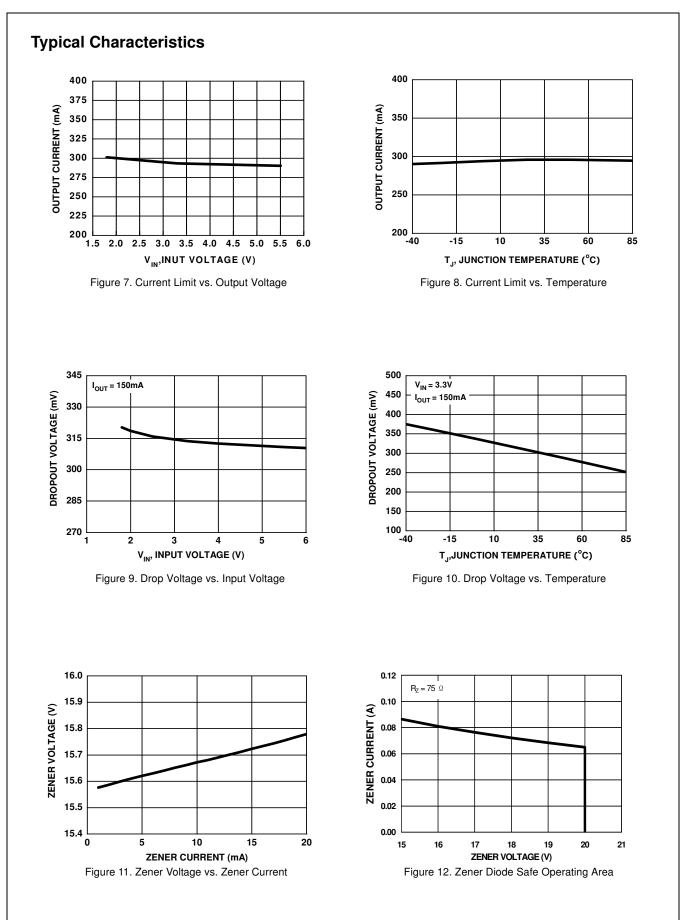
Parameter	Symbol	ol Conditions		Min	Тур	Max	Units		
Basic Operation									
Operating Voltage	V _{IN}			1.8	-	5.5	V		
Ouissesset Oursest	Ι _Q	I _{OUT} = 0mA	V _{IN} = 1.8 to 3.3V	-	95	-			
Quiescent Current		V _{ON} ACTIVE	V _{IN} = 3.3 to 5.5V	-	110	200	μA		
Shutdown Current	I _{SHDN}	$V_{ON} = 0V, I_{OUT} = 0mA$		-	-	1	μA		
Latch-off Current	I _{LATCHOFF}	V _{ON} =V _{IN} , after a	n overcurrent fault	-	50	-	μA		
Reverse Block Leakage Current	I _R	$V_{OUT} = 12V, V_{IN} = V_{ON} = 0V,$ $T_A = 25 ^{\circ}\text{C}$		-	-	10	μA		
Reverse Breakdown Voltage		I _{OUT} = 1mA		-	15	-	V		
	V _{DROP}	T _A = 25 °C, I _{OUT} = 150mA		-	0.3	0.4			
Dropout Voltage		T _A = 85 °C, I _{OUT} = 150mA			0.23	-	V		
		T _A = -40 °C, I _{OUT} = 150mA		-	0.36	-			
ON Input Logic	VIH	V _{IN} = 1.8V V _{IN} = 5.5V		0.75	-	-	V		
High Voltage (ON)	ЧH			1.3	-	-			
ON Input Logic Low	N Input Logic Low V _{IL} V _{IN} = 1.8V			-	-	0.5	v		
Voltage		V _{IN} = 5.5V		-	-	1.0	v		
ON Input Leakage		V _{ON} = V _{IN} or GND		-	-	1	μA		
Off Switch Lookaga	ISWOFF	V _{ON} = 0V, V _{OUT} = 0V @ V _{IN} = 5.5V, T _A = 85 ℃				1	μA		
Off Switch Leakage		V _{ON} = 0V, V _{OUT} = @ V _{IN} = 3.3V, T _A			10	100	nA		
		$V_{IN} = 5V, I_{SINK} =$	10mA	-	-	- 0.2 V			
FLAGB Output Logic Low Voltage		$V_{IN} = 1.8V, I_{SINK}$	= 10mA	-	-	0.3	ľ		
FLAGB Output High Leakage Current		V _{IN} = 5V, Switch on		-	-	1	μA		

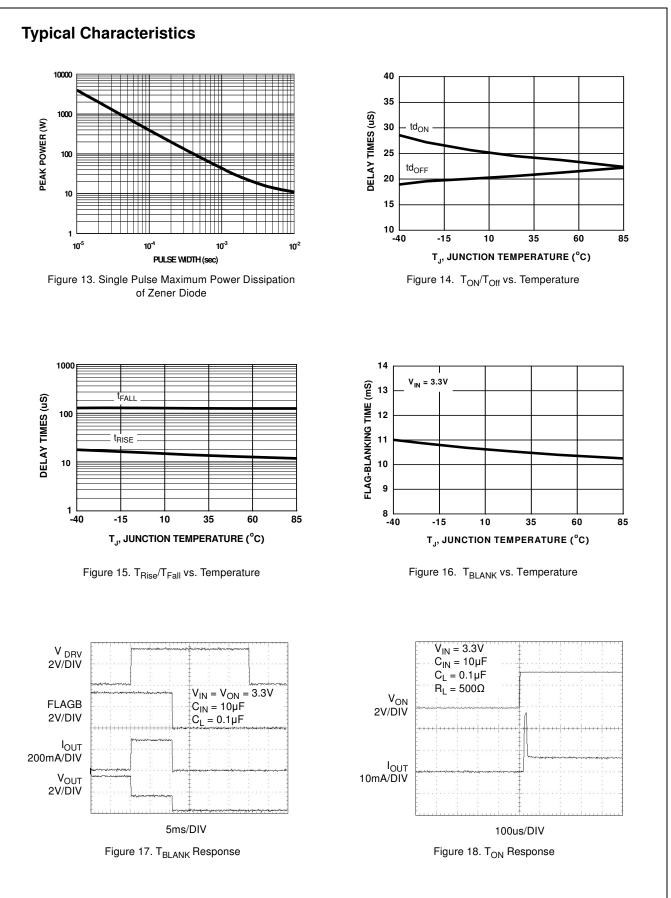
FPF2174
IntelliMAX TM
Advanced Load N
Load
Management Products
Products

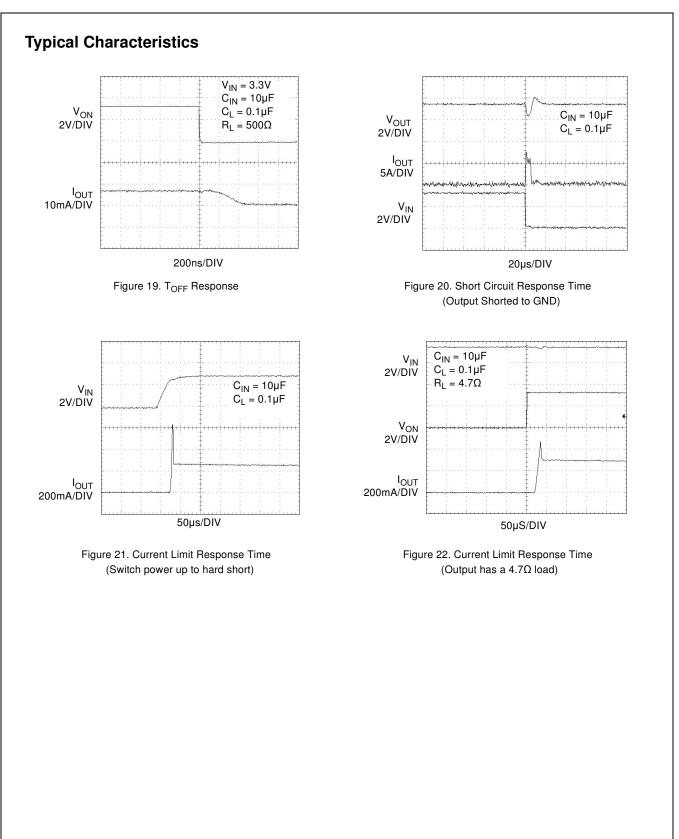
Parameter	Symbol	Conditions	Min	Тур	Max	Units
Protections		•	•			
Current Limit	I _{LIM}	V _{IN} = 3.3V	200	300	400	mA
		Shutdown Threshold	-	140	-	
Thermal Shutdown		Return from Shutdown	-	130	-	°C
		Hysteresis	-	10	-	1
Under Voltage Shutdown	UVLO	V _{IN} Increasing	1.5	1.6	1.7	V
Under Voltage Shutdown Hysteresis			-	47	-	mV
Zener Clamp Voltage	VZ	$I_Z = 1mA$	-	15.58	-	V
Zener Leakage	Ι _Ζ	V _Z = 12V	-	-	10	μA
Dynamic						
Delay On Time	td _{ON}	$R_L = 500\Omega, \ C_L = 0.1 \mu F$	-	25	50	μs
Delay Off Time	td _{OFF}	$R_L = 500\Omega,\ C_L = 0.1 \mu F$	-	20	40	μs
V _{OUT} Rise Time	t _R	$R_L = 500\Omega, \ C_L = 0.1 \mu F$	-	14	30	μs
V _{OUT} Fall Time	t _F	$R_L = 500\Omega, \ C_L = 0.1 \mu F$	-	126	250	μs
Over Current Blanking Time	t _{BLANK}		5	10	20	ms
Short Circuit Response Time		V _{IN} = V _{ON} = 3.3V. Moderate Over-Current Condition.	-	3	-	μs
		V _{IN} = V _{ON} = 3.3V. Hard Short.	-	20	-	ns

Note 1: Package power dissipation on 1 square inch pad, 2 oz. copper board.









Description of Operation

The FPF2174 is a current limited switch that protects systems and loads which can be damaged or disrupted by the application of high currents. The core of the device is a 0.125Ω P-channel MOSFET and a controller capable of functioning over a wide input operating range of 1.8-5.5V paired with a low forward voltage drop Schottky diode for reverse blocking and a 16V zener diode for output clamp. The controller protects against system malfunctions through current limiting, undervoltage lockout and thermal shutdown. The current limit is preset for 200mA.

On/Off Control

The ON pin controls the state of the switch. Activating ON continuously holds the switch in the on state so long as there is no under-voltage on V_{IN} or a junction temperature in excess of 150 °C. ON is active HI and has a low threshold making it capable of interfacing with low voltage signals. When the MOSFET is off, the Schottky diode acts as a barrier so that no reverse current can flow when V_{OUT} is greater than V_{IN} .

Fault Reporting

Upon the detection of an over-current, an input under-voltage, or an over-temperature condition, the FLAGB signals the fault mode by activating LO. The FLAGB goes LO at the end of the blanking time and is latched LO and ON must be toggled to release it. FLAGB is an open-drain MOSFET which requires a pull-up resistor between V_{IN} and FLAGB. During shutdown, the pull-down on FLAGB is disabled to reduce current draw from the supply.

Current Limiting

The current limit guarantees that the current through the switch doesn't exceed a maximum value while not limiting at less than a minimum value. The minimum current is 200mA and the maximum current is 400mA. The device has a blanking time of 10ms, nominally, during which the switch will act as a constant current source. At the end of the blanking time, the switch will be turned-off and the FLAGB pin will activate to indicate that current limiting has occurred.

Under-Voltage Lockout

The under-voltage lockout turns-off the switch if the input voltage drops below the under-voltage lockout threshold. With the ON pin active the input voltage rising above the under-voltage lockout threshold will cause a controlled turn-on of the switch which limits current over-shoots.

Thermal Shutdown

The thermal shutdown protects the die from internally or externally generated excessive temperatures. During an overtemperature condition the FLAGB is activated and the switch is turned-off. The switch automatically turns-on again if temperature of the die drops below the threshold temperature.

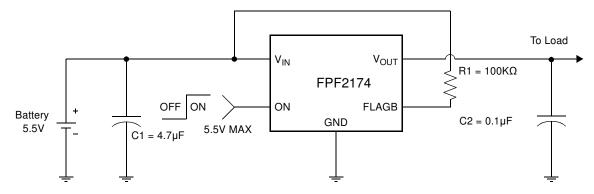
Transient Safe Operating Area of Zener Diode

Integrated zener diode is designed to protect systems from a transient over voltage stress resulting from a flyback voltage (L*di/dt) such as connecting the output of switch to an active rails.

When the transient voltage exceed the zener threshold (Vz) the zener starts conducting and prevents the output of loadswitch from experiencing those transient over voltages and protects any reverse current from flowing through the switch. For reliable operation, user should not exceed the SOA curve shown in Figure 13.

Application Information

Typical Application



Input Capacitor

To limit the voltage drop on the input supply caused by transient in-rush currents when the switch turns-on into a discharged load capacitor or a short-circuit, a capacitor needs to be placed between V_{IN} and GND. A 4.7 μ F ceramic capacitor, C_{IN}, placed close to the pins is usually sufficient. Higher values of C_{IN} can be used to further reduce the voltage drop.

Output Capacitor

A 0.1uF capacitor C_{OUT} , should be placed between V_{OUT} and GND. This capacitor will prevent parasitic board inductances from forcing V_{OUT} below GND when the switch turns-off.

Power Dissipation

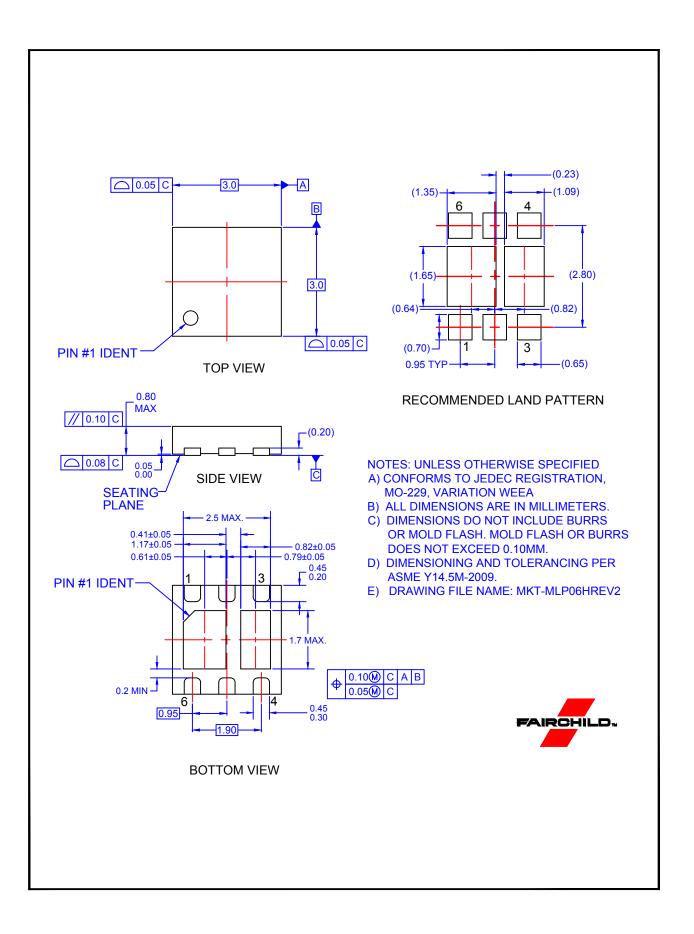
During normal operation as a switch, the power dissipation is small and has little effect on the operating temperature of the part. The parts with the higher current limits will dissipate the most power and that will only be typically,

$$P = I_{LIM} \times V_{DROP} = 0.4 \times 0.4 = 160 \text{mW}$$
 (2)

When using the part, attention must be given to the manual resetting of the part. Continuously resetting the part at a high duty cycle when a short on the output is present can cause the temperature of the part to increase. The junction temperature will only be allowed to increase to the thermal shutdown threshold. Once this temperature has been reached, toggling ON will not turn-on the switch until the junction temperature drops.

Board Layout

For best performance, all traces should be as short as possible. To be most effective, the input and output capacitors should be placed close to the device to minimize the effects that parasitic trace inductances may have on normal and short-circuit operation. Using wide traces for V_{IN}, V_{OUT} and GND will help minimize parasitic electrical effects along with minimizing the case to ambient thermal impedance.



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